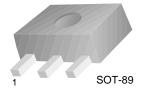


### KSD1621

## **High Current Driver Applications**

- Low Collector-Emitter Saturation Voltage
- Large Current Capacity and Wide SOA
- Fast Switching Speed
- Complement to KSB1121



### 1. Base 2. Collector 3. Emitter

## **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	30	V
$V_{CEO}$	Collector-Emitter Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	2	А
P <sub>C</sub>	Collector Power Dissipation	500	mW
P <sub>C</sub> *		1.3	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

<sup>\*</sup> Mounted on Ceramic Board (250mm<sup>2</sup>x0.8mm)

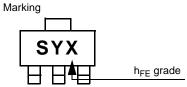
### **Electrical Characteristics** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C}=10\mu A, I_{E}=0$	30			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =1mA, I <sub>B</sub> =0	25			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E=10\mu A, I_C=0$	6			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =20V, $I_E$ =0			100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE}=4V$ , $I_{C}=0$			100	nA
h <sub>FE1</sub>	DC Current Gain	V <sub>CE</sub> =2V, I <sub>C</sub> =0.1A	100		560	
h <sub>FE2</sub>		$V_{CE}=2V$ , $I_{C}=1.5A$	65			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =1.5A, I <sub>B</sub> =75mA		0.18	0.4	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =1.5A, I <sub>B</sub> =75mA		0.85	1.2	V
f <sub>T</sub>	Current Gain Bandwidth product	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA		150		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		19		pF
t <sub>ON</sub>	* Turn On Time	V <sub>CC</sub> =12V, V <sub>BE</sub> =5V		60		ns
t <sub>STG</sub>	* Storage Time	$I_{B1} = -I_{B2} = 25 \text{mA}$		500		ns
t <sub>F</sub>	* Fall Time	$I_C$ =0.5A, $R_L$ =25 $\Omega$		25		ns

<sup>\*</sup> Pulse Width=20μs, Duty Cycle≤1%

## **h**<sub>FE</sub> Classification

Classification	R	S	Т	U
h <sub>FE</sub>	100 ~ 200	140 ~ 280	200 ~ 400	280 ~ 560



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# **Typical Characteristics**

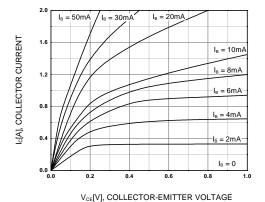


Figure 1. Static Characteristic

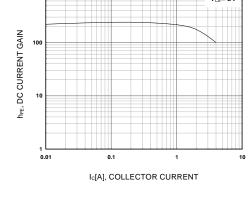


Figure 2. DC current Gain

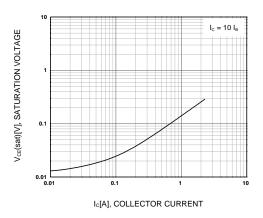


Figure 3. Collector-Emitter Saturation Voltage

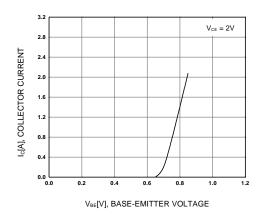


Figure 4. Base-Emitter On Voltage

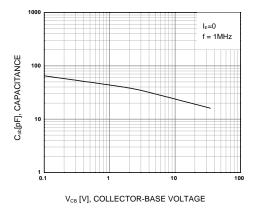


Figure 5. Collector Output Capacitance

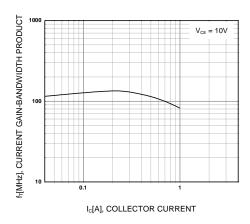


Figure 6. Current Gain Bandwidth Product

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# Typical Characteristics (Continued)

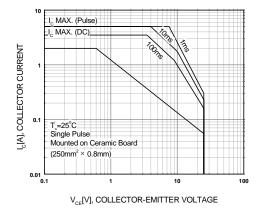


Figure 7. Safe Operating Area

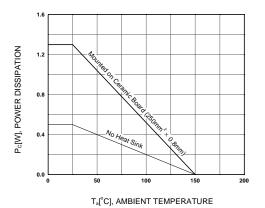
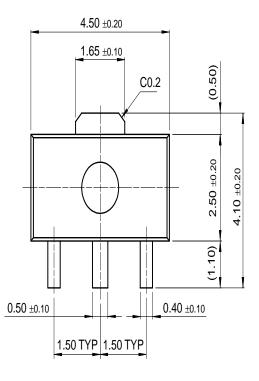
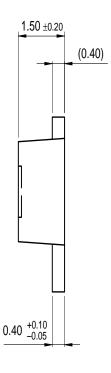


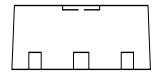
Figure 8. Power Derating

# **Package Dimensions**

# **SOT-89**







Dimensions in Millimeters

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E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I <sup>2</sup> C™	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board. Around the world.™		OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	$VCX^{TM}$
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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